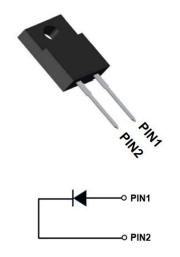






Silicon Carbide Schottky Diode

V_{RRM}	650V
I _{F(135°C)}	4A
Q _C	12.5nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

 Package: ITO-220AC
 Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free

• Terminals: Tin plated leads

• Polarity: As marked

■Maximum Ratings (T_C=25°C Unless otherwise specified)

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D106504FG1
Reverse voltage (Repetitive peak) @ T _j =25°C	V_{RRM}	V	650
Reverse voltage (Surge peak) @ T _j =25°C	V_{RSM}	V	650
Reverse voltage (DC) @ T _j =25°C	V_{DC}	V	650
Continuous forward current @ T _C =25°C	I _F	А	9
Continuous forward current @ T _C =135°C	IF.		4
Non-repetitive peak forward surge current @ T _C =25°C, tp=10ms, Half Sine Wave	I _{FSM}	А	32
Power Dissipation@ T _C =25°C		10/	27
Power Dissipation@ T _C =110°C	Р _{тот}	W	12
i²t Value@ Tc=25°C ,tp=10ms	∫ i²dt	A ² S	5.1
Operating junction and Storage temperature range	T_{j} , T_{stg}	°C	-55 to +175





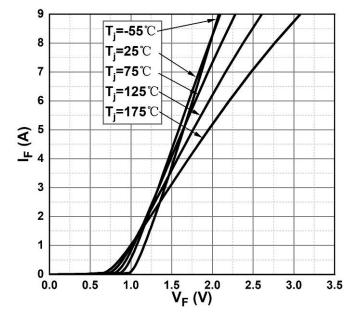
■Electrical Characteristics

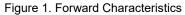
PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.
Forward voltage drop	V _F	V	I _F =4A, T _j =25°C	1.46	1.55
			I _F =4A, T _j =175°C	1.75	-
Reverse leakage current	I _R	μA	V _R =650V, T _j =25°C	0.5	20
			V _R =650V, T _j =175°C	30	-
Total capacitive charge	Q _c	nC	$\begin{array}{c} V_R \!\!=\!\! 400 V, T_j \!\!=\!\! 25^\circ C \; , \\ Q_C \!\!=\!\! \int_0^{VR} \!\! C(V) \! dV \end{array} \label{eq:VR}$	12.5	-
Total capacitance	С	pF	V _R =0V, f=1MHZ	266	-
			V _R =200V, f=1MHZ	24	-
			V _R =400V, f=1MHZ	19	-
Capacitance Stored Energy	Ec	μJ	V _R =400V	1.6	-

■Thermal Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	$R_{\theta J\text{-}C}$	°C W	5.46

■Typical Characteristics





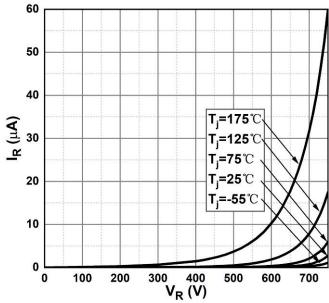
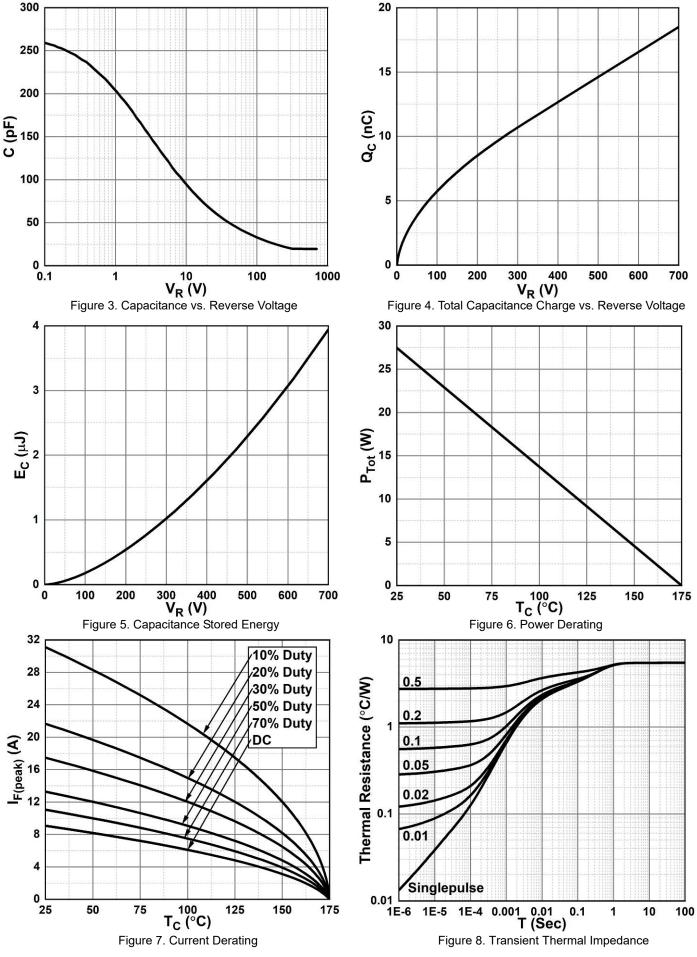


Figure 2. Reverse Characteristics



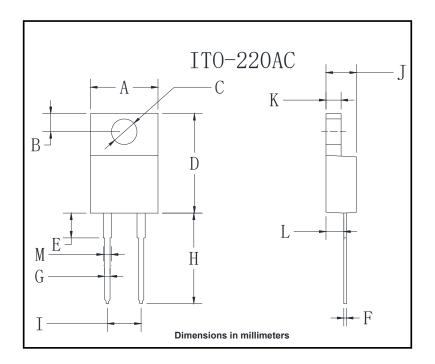








■Outline Dimensions



ITO-220AC				
Dim	Min	Max		
Α	9.8	10.2		
В	2.25	2.75		
С	2.95	3.45		
D	14.75	15.25		
Е	3.5	4.1		
F	0.45	0.75		
G	0.45	0.75		
Н	13.35	14.15		
I	4.97	5.23		
J	4.3	4.8		
K	2.5	2.74		
L	2.58	2.82		
М	1.03	1.43		



YJD106504FG1



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